

4M x 1 and 1M x 4 DRAM

FEATURES

- Industry Standard Pinouts
- 50, 60, 70 or 80ns RAS Access Time (tRAC)
- Static Column Mode or Enhanced Page Mode
- RAS-Only Refresh, Hidden Refresh and CAS-before-RAS Refresh
- Battery Backup Mode with Automatic Refresh
- Test Mode
- Commercial Voltage/Temperature Range
 - 4.5 - 5.5 Volts Vcc
 - 0 - 70°C Operating Temperature
- Packages - 20 Pin 300mil PDIP
 - 26 Pin SOJ
 - 20 Pin ZIP

See pages 11 and 12 for Package
and Pinout details

AAA4M200 SERIES

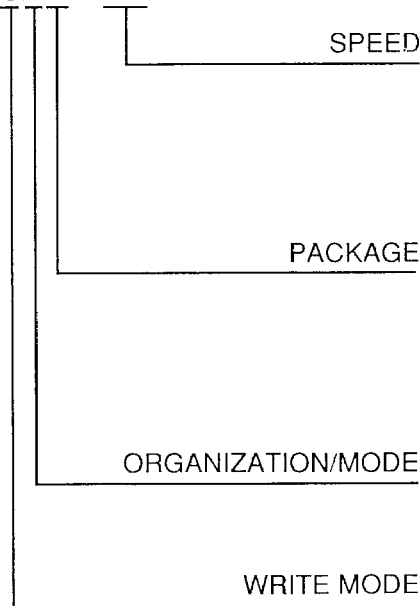
Part Number	tRAC ¹	tCAC ²	tAA ³ (tCAA)	tRC ⁴	tPC ⁵	Icc ⁶ (Standby)	Icc ⁷ (Battery Backup)	Icc ⁸ (Active)	Refresh ⁹ (tREF)
4M x 1 AND 1M x 4 - STATIC COLUMN AND ENHANCED PAGE MODE									
AAA4M20XX-05	50ns	13ns	25ns	100ns	30ns	1mA	200µA	100mA	16ms
AAA4M20XX-06	60ns	15ns	30ns	110ns	35ns	1mA	200µA	90mA	16ms
AAA4M20XX-07	70ns	20ns	35ns	130ns	40ns	1mA	200µA	80mA	16ms
AAA4M20XX-08	80ns	20ns	40ns	150ns	45ns	1mA	200µA	70mA	16ms

NOTES:

1. tRAC defines maximum RAS Access Time.
2. tCAC defines maximum CAS Access Time.
3. tAA (alternatively tCAA) defines maximum Column Address Access Time.
4. tRC defines minimum Read or Write Cycle Time.
5. tPC defines minimum Enhanced Page Mode or Static Column Mode Cycle Time.
6. Icc (Standby) defines maximum Vcc supply current with inputs at CMOS levels and RAS, CAS ≥ Vcc - 0.2V.
7. Icc (Battery Backup) defines maximum Vcc supply current while in Battery Backup Mode with CAS ≤ VIL, other inputs at CMOS levels. Refer to Data Sheet for details.
8. Icc (Active) defines maximum Vcc supply current under normal operation with tRC = tRC min., 4.5 ≤ Vcc ≤ 5.5 volts and 0°C ≤ Ta ≤ 70°C.
9. tREF defines the Refresh Interval during which all internal rows (1024) must be refreshed when not in Battery Backup Mode.

ORDERING INFORMATION:

AAA4M20XX - XX



05: 50ns tRAC
06: 60ns tRAC
07: 70ns tRAC
08: 80ns tRAC

J: SOJ
P: PDIP
Z: ZIP
S: TSOP (I) Normal Bend
Q: TSOP (I) Reverse Bend
T: TSOP (II) Normal Bend
R: TSOP (II) Reverse Bend

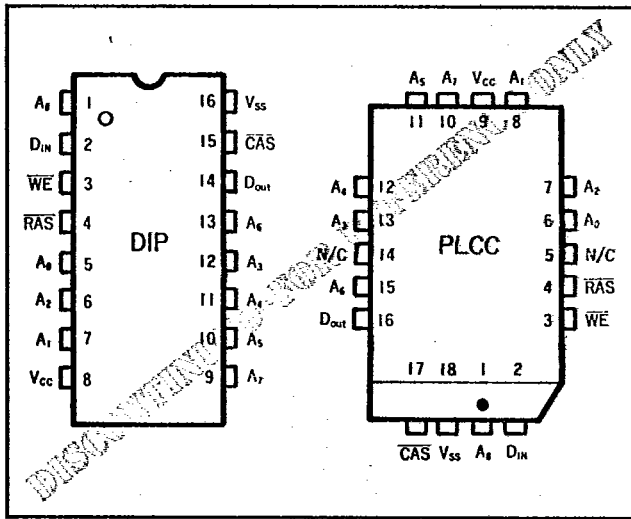
0: 4M x 1 Enhanced Page Mode
1: 4M x 1 Static Column Mode
4: 1M x 4 Enhanced Page Mode
5: 1M x 4 Static Column Mode

0: No Write Per Bit
1: Write Per Bit (To be announced)

PACKAGE AND PINOUT DETAILS

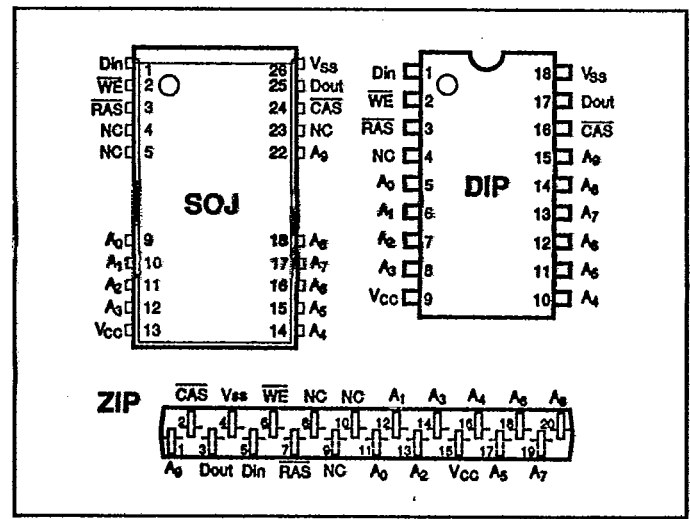
N M B/ SEMICONDUCTOR DIV 45E D ■ 6429234 0000336 7 ■ NMB

AAA2800 SERIES - 256K x 1

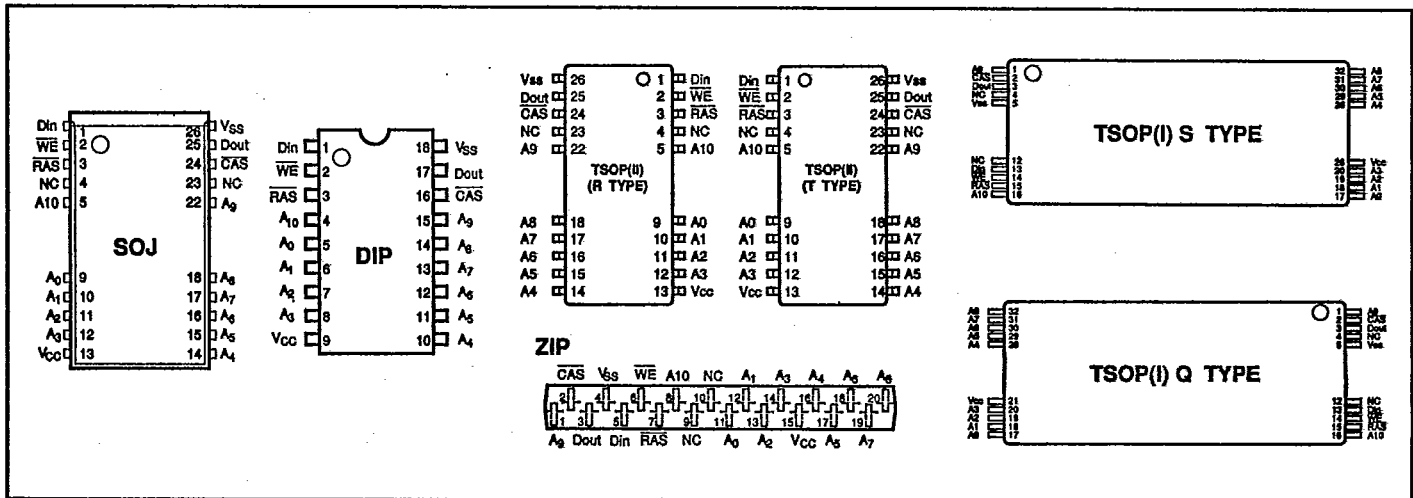


AAA1M300 SERIES - 1M x 1

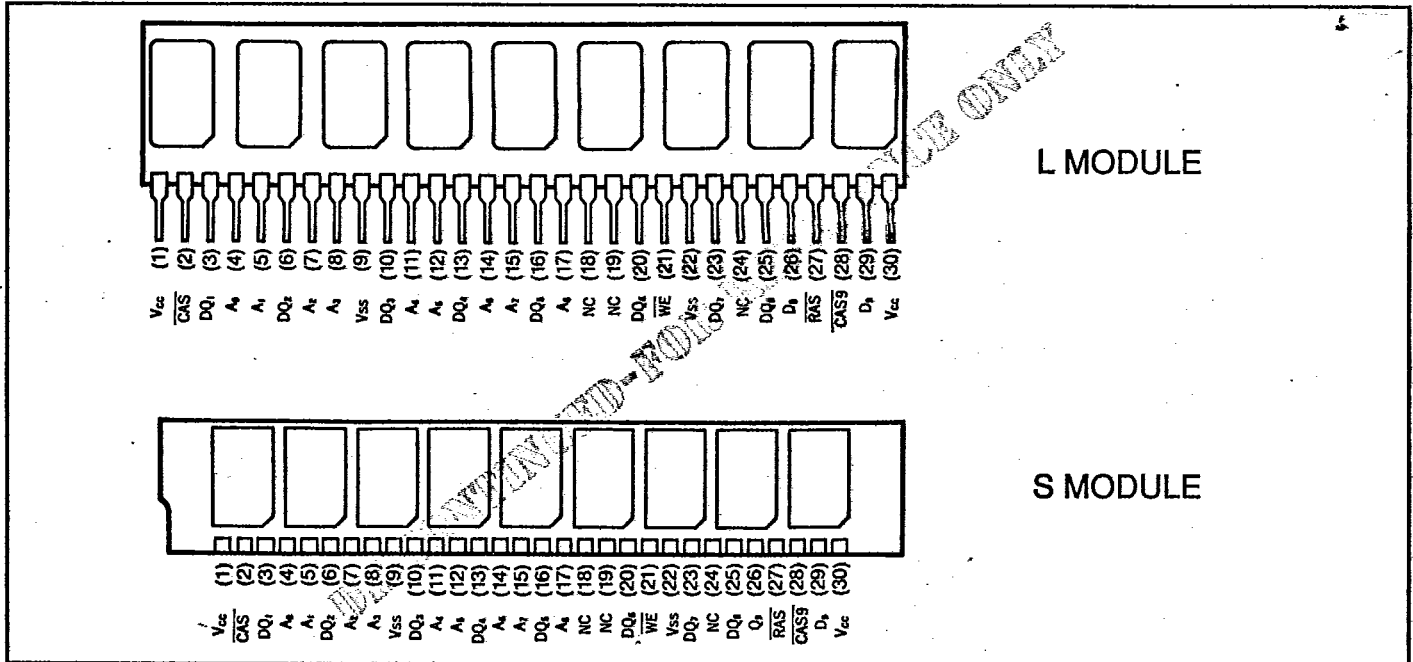
T-91-20



AAA4M200 SERIES - 4M x 1



MM2800 J8/J9 SERIES - 256K x 8/9

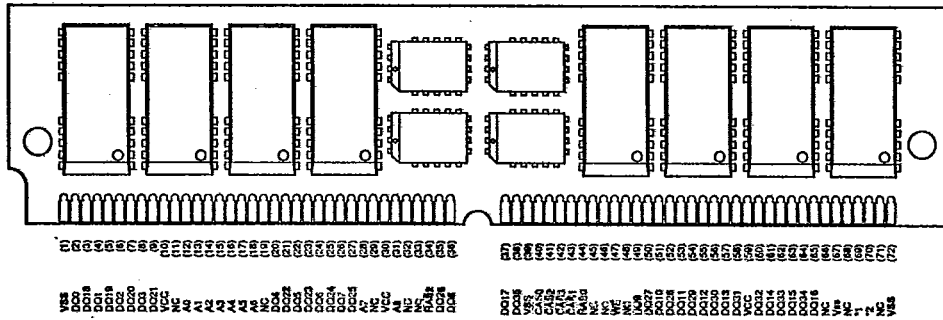


PACKAGE AND PINOUT DETAILS

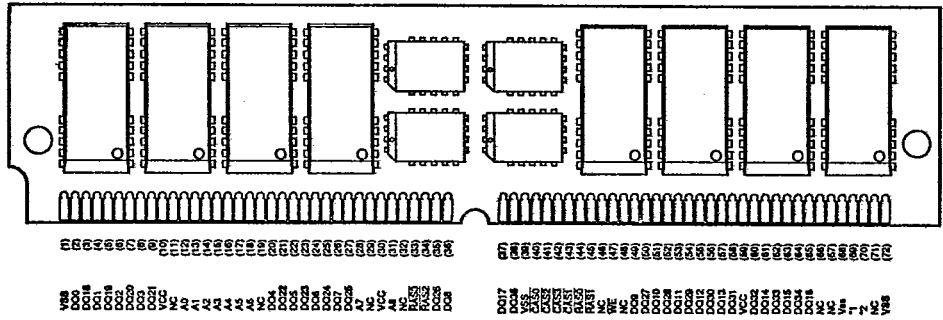
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MM256K0J36/MM512K0J36 SERIES - 256K x 36 and 512K x 36

256K x 36
(Components on one side of PCB)



512K x 36
(Components on both sides of PCB)



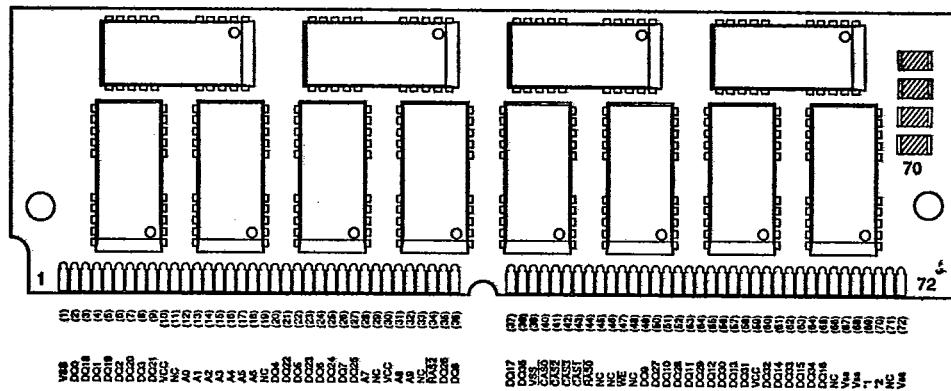
Pinout Variations

	-06	-07	-08
*1	TBD	V _{ss}	NC
*2	TBD	NC	V _{ss}

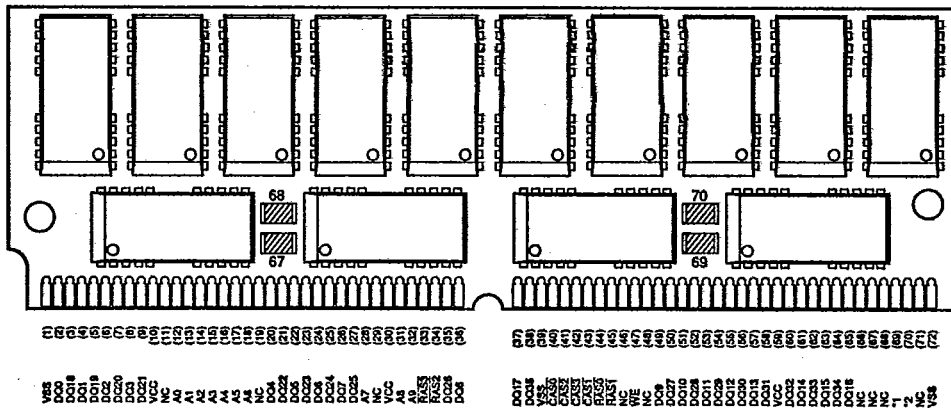
Note: TBD: To be determined

MM1M0J36/MM2M0J36 - 1M x 36 and 2M x 36

1M x 36
(Components on one side of PCB)



2M x 36
(Components on both sides of PCB)



Pinout Variations

	-06	-07	-08
*1	TBD	V _{ss}	NC
*2	TBD	NC	V _{ss}

Note: TBD: To be determined

PACKAGE AND PINOUT DETAILS

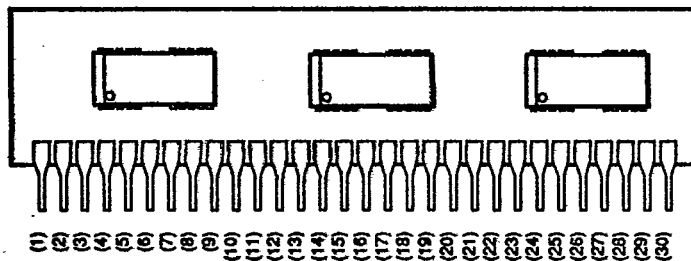
N M B/ SEMICONDUCTOR DIV 45E D ■ 6429234 0000339 2 ■ NMBT-91-20

MM256K0J8R/J9R SERIES - (3 CHIP "R" VERSION)

MM1M0J8/J9 SERIES - (3 CHIP VERSION)

MM1M0J8R/J9R SERIES - (3 CHIP "R" VERSION)

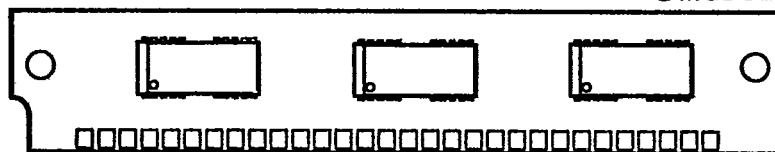
L MODULE



(1) (2) (3) (4) (5) (6) (7) (8) (9) (10) (11) (12) (13) (14) (15) (16) (17) (18) (19) (20) (21) (22) (23) (24) (25) (26) (27) (28) (29) (30)

V_{CC} CAS₁ A₀ A₁ DO₂ A₂ A₃ V_{SS} DO₃ A₄ A₅ DO₄ A₆ A₇ DO₅ A₈ NC NC DO₆ WE V_{SS} DO₇ NC DO₈ Q₉ RAS₁ CAS₂ D_p V_{CC}

S MODULE



(1) (2) (3) (4) (5) (6) (7) (8) (9) (10) (11) (12) (13) (14) (15) (16) (17) (18) (19) (20) (21) (22) (23) (24) (25) (26) (27) (28) (29) (30)

V_{CC} CAS₁ DO₁ A₀ A₁ DO₂ A₂ A₃ V_{SS} DO₃ A₄ A₅ DO₄ A₆ A₇ DO₅ A₈ NC NC DO₆ WE V_{SS} DO₇ NC DO₈ Q₉ RAS₁ CAS₂ D_p V_{CC}

Pinout 18 Variations

256K x 8/9	3 Chip "R"	N/C
1M x 8/9	3 Chip	A9
1M x 8/9	3 Chip "R"	A9

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